TAIWAN SEMICONDUCTOR

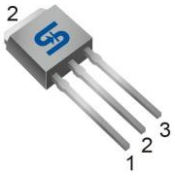
TSM60N900

600V, 4.5A, 0.9Ω
N-Channel Power MOSFET

Pb-Free RoHS COMPLIANT

ITO-220

TO-251 (IPAK)



Pin Definition:
1. Gate
2. Drain
3. Source

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	600	V
$R_{DS(on)}$ (max)	0.9	Ω
Q_g	9.7	nC

TO-252 (DPAK)

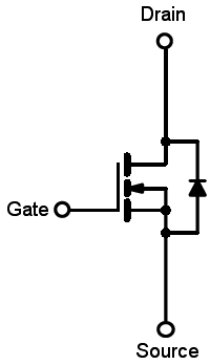
Features

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

Application

- Power Supply.
- Lighting

Block Diagram



N-Channel MOSFET

Ordering Information

Part No.	Package	Packing
TSM60N900CI C0G	ITO-220	50pcs / Tube
TSM60N900CH C5G	TO-251	75pcs / Tube
TSM60N900CP ROG	TO-252	2.5kpcs / 13” Reel

Note: “G” denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit
			ITO-220	IPAK/DPAK	
Drain-Source Voltage		V_{DS}	600		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current (Note 1)	T_C = 25°C	I_D	4.5		A
Pulsed Drain Current (Note 2)		I_{DM}	13.5		A
Total Power Dissipation @ T_C = 25°C		P_{DTOT}	20	50	W
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	81		mJ
Single Pulsed Avalanche Current (Note 3)		I_{AS}	1.8		A
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150		°C

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Thermal Performance

Parameter	Symbol	Limit		Unit
		ITO-220	IPAK/DPAK	
Junction to Case Thermal Resistance	$R_{\Theta JC}$	6.25	2.5	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62		°C/W

Electrical Specifications (T_C = 25°C unless otherwise noted)

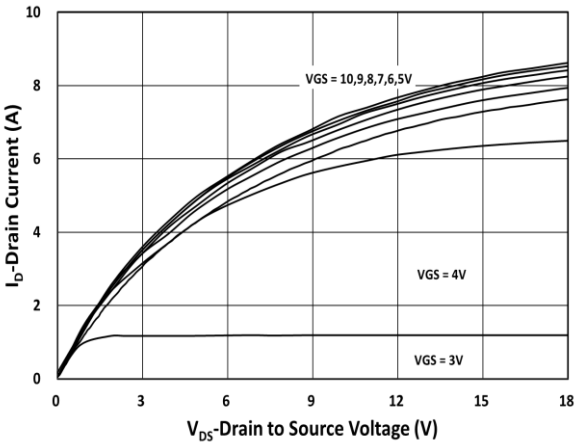
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static (Note 4)						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	$V_{GS(TH)}$	2	3	4	V
Gate Body Leakage	V_{GS} = ±30V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = 600V, V_{GS} = 0V	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	V_{GS} = 10V, I_D = 2.3A	$R_{DS(ON)}$	--	0.72	0.9	Ω
Dynamic (Note 5)						
Total Gate Charge	V_{DS} = 380V, I_D = 2.3A, V_{GS} = 10V	Q_g	--	9.7	--	nC
Gate-Source Charge		Q_{gs}	--	2.3	--	
Gate-Drain Charge		Q_{gd}	--	3.6	--	
Input Capacitance	V_{DS} = 100V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	480	--	pF
Output Capacitance		C_{oss}	--	36	--	
Gate Resistance	f=1MHz, open drain	R_g	--	3.4	--	Ω
Switching (Note 6)						
Turn-On Delay Time	V_{DD} = 380V, R_{GEN} = 4.7Ω, I_D = 2.3A, V_{GS} = 10V,	$t_{d(on)}$	--	12	--	ns
Turn-On Rise Time		t_r	--	16	--	
Turn-Off Delay Time		$t_{d(off)}$	--	22	--	
Turn-Off Fall Time		t_f	--	12	--	
Source-Drain Diode (Note 4)						
Forward On Voltage	I_S=4.5A, V_{GS}=0V	V_{SD}	--	--	1.4	V
Reverse Recovery Time	V_R=200V, I_S=2.3A dI$_F$/dt=100A/μs	t_{rr}	--	179	--	ns
Reverse Recovery Charge		Q_{rr}	--	1.2	--	μC

Notes:

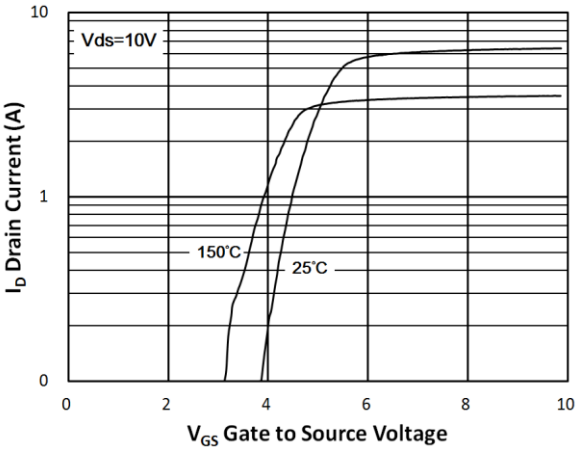
1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. L=50mH, I_{AS}=1.8A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
4. Pulse test: PW ≤ 300μs, duty cycle ≤ 2%
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

Electrical Characteristics Curves

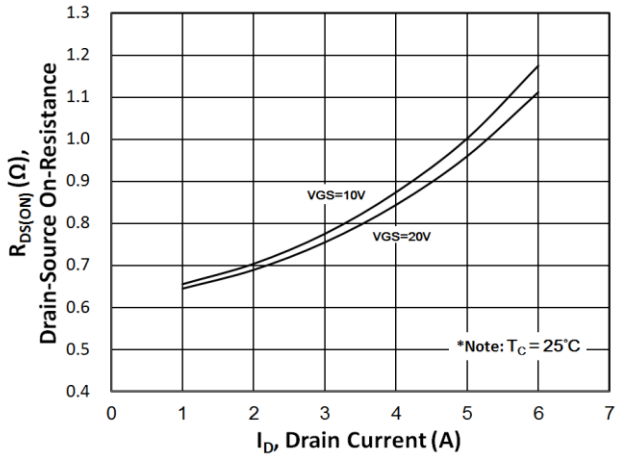
Output Characteristics



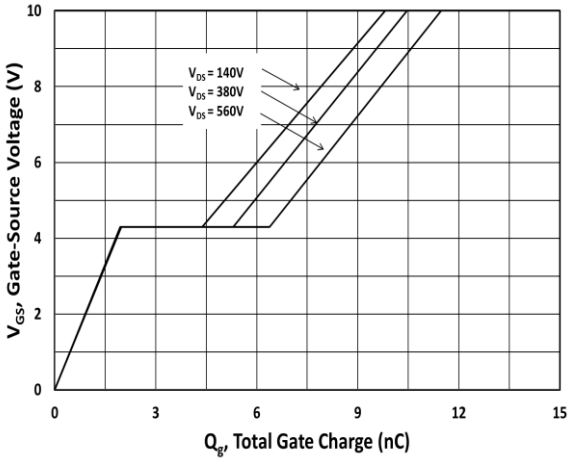
Transfer Characteristics



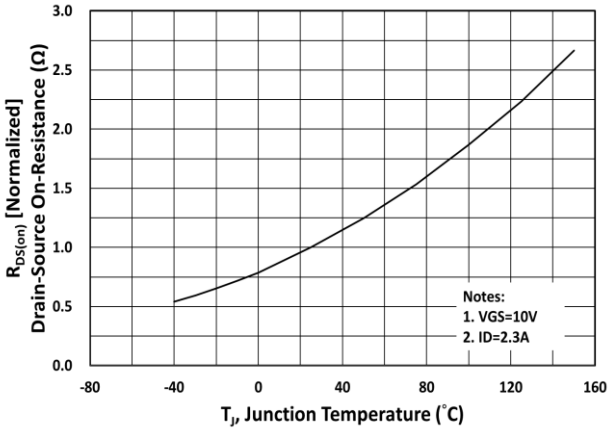
On-Resistance vs. Drain Current



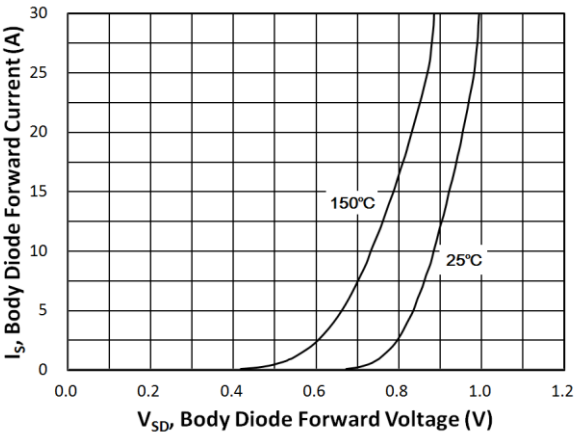
Gate Charge vs. Gate-Source Voltage



On-Resistance vs. Junction Temperature

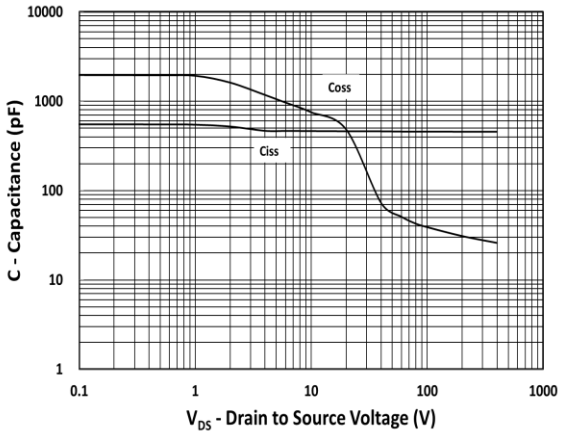


Source-Drain Diode Forward Voltage vs. Current

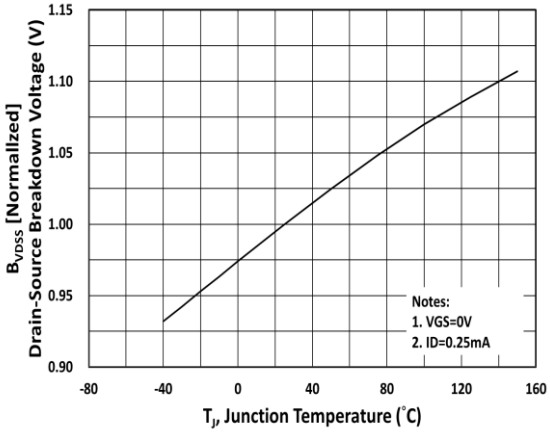


Electrical Characteristics Curves

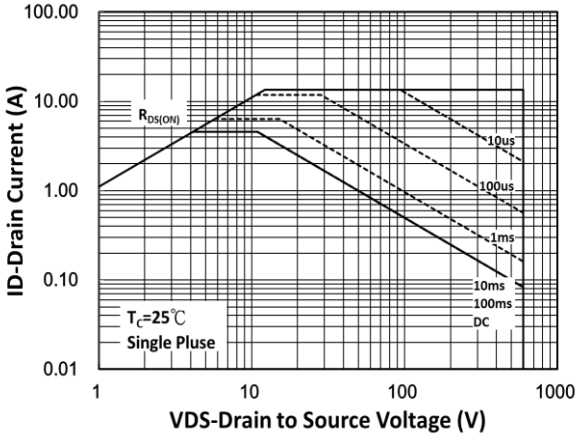
Capacitance vs. Drain-Source Voltage



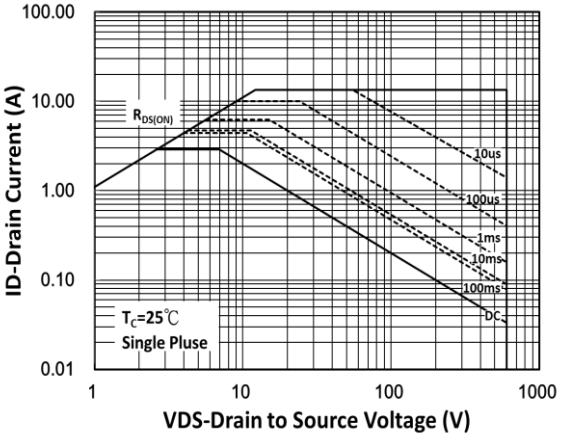
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (DPAK/IPAK)

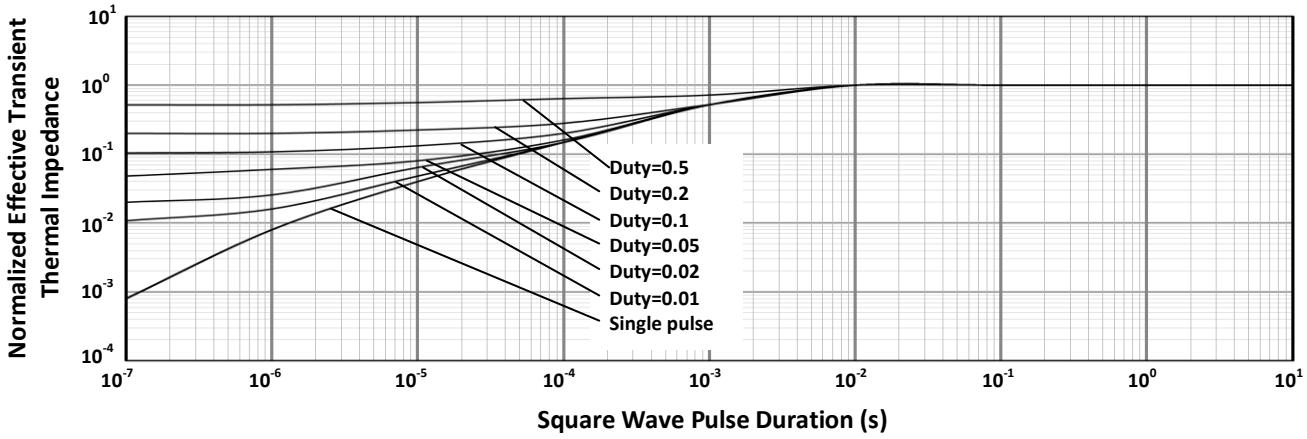


Maximum Safe Operating Area (ITO-220)

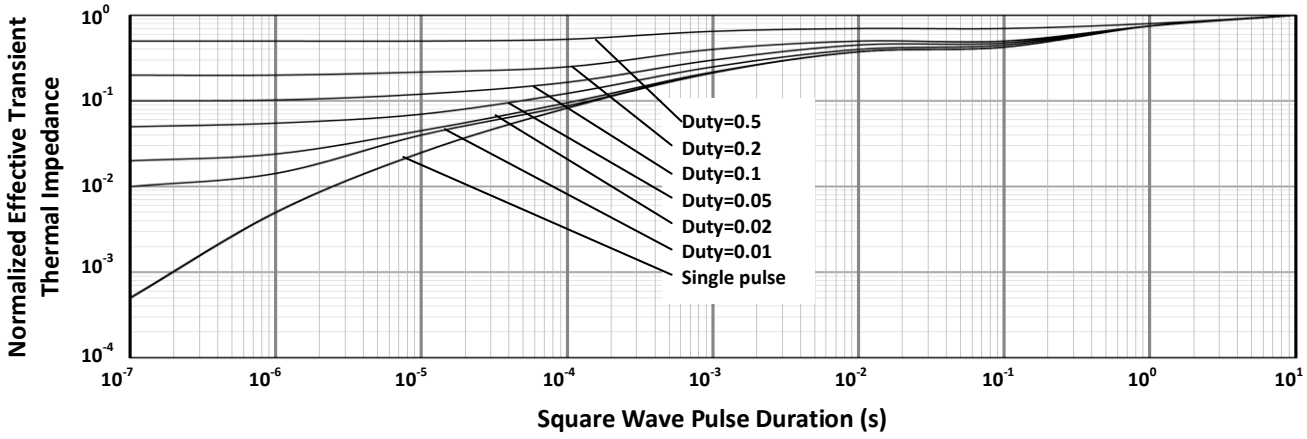


Electrical Characteristics Curves

Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)



Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)



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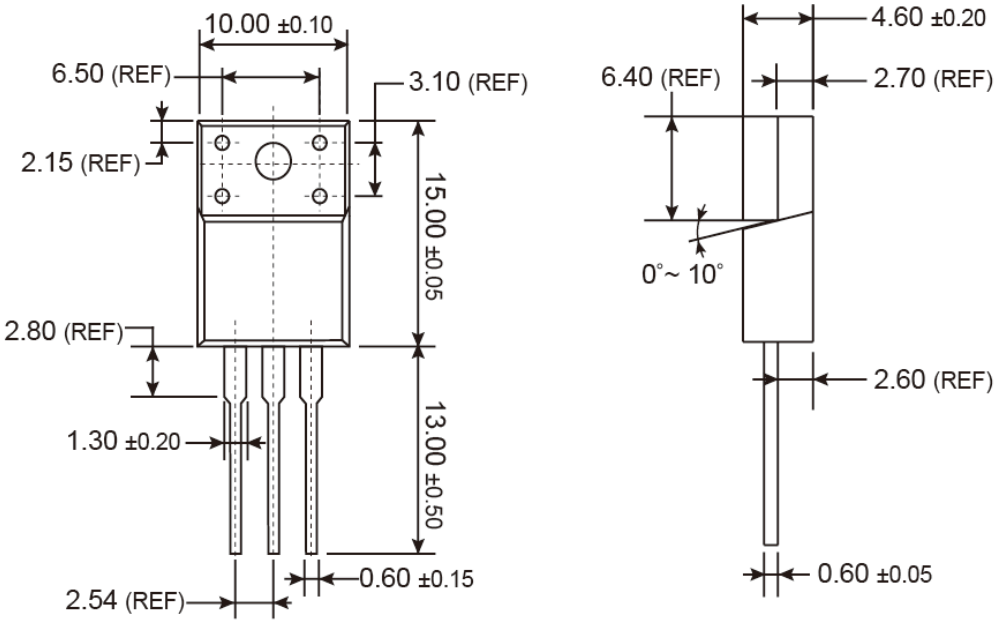
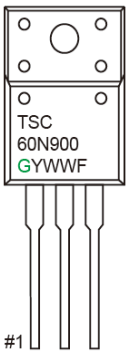
ITO-220 Mechanical Drawing



Unit: Millimeters

Marking Diagram



G = Halogen Free
Y = Year Code
WW = Week Code (01~52)
F = Factory Code

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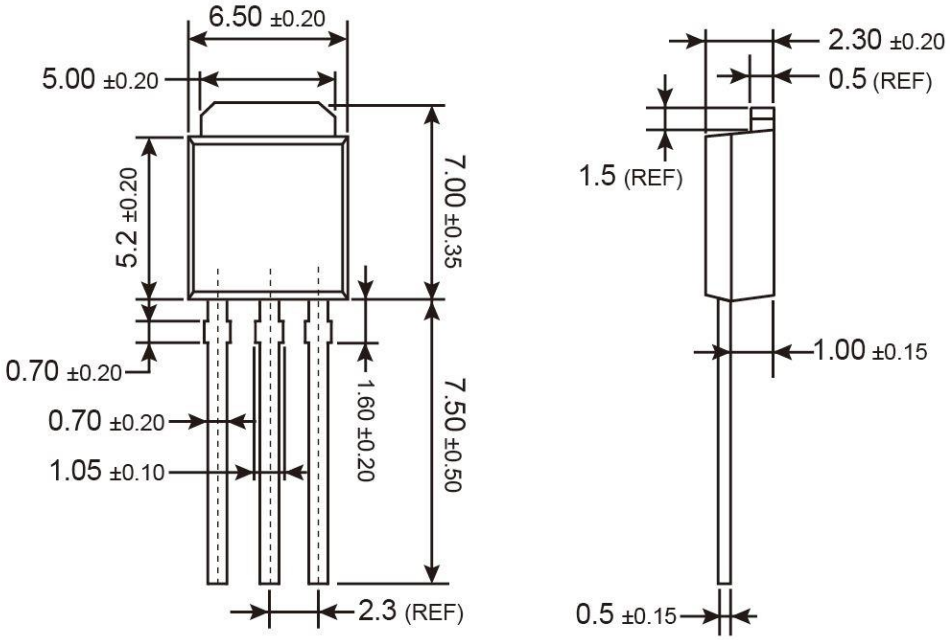
TO-251 (IPAK) Mechanical Drawing



Unit: Millimeters

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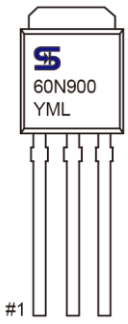

Y = Year Code

M = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apl, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)

L = Lot Code

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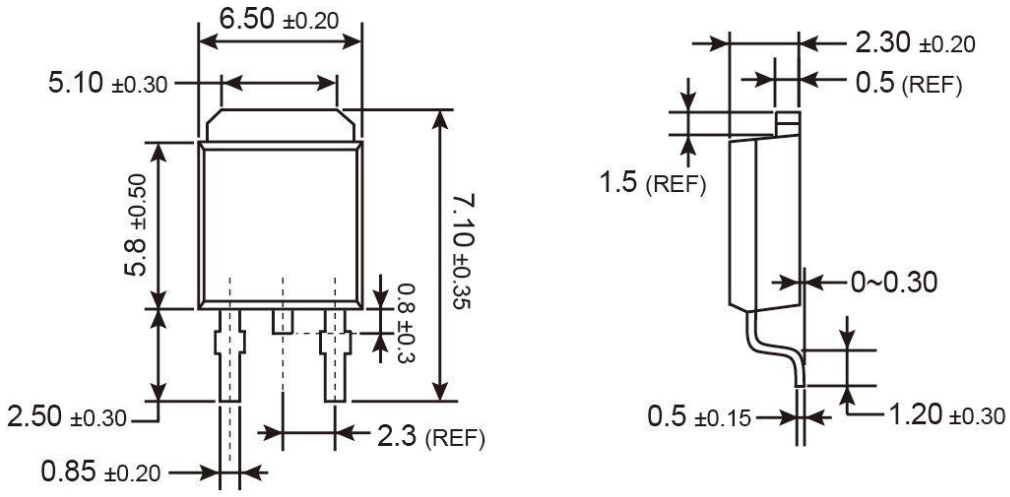
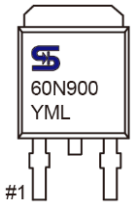
TO-252 (DPAK) Mechanical Drawing



Unit: Millimeters

Marking Diagram



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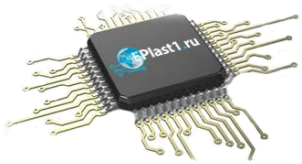
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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